L Number	Hits	Search Text	DB	Time stamp
1	2890	((257/288) or (257/408) or (257/409) or (257/410) or (257/411) or (438/230)).CCLS.	USPAT; US-PGPUB	2004/10/19 08:37
2	3	(((257/288) or (257/408) or (257/409) or (257/410) or (257/411) or (438/230)).CCLS.) and "without" near3 (ammonia "NH.sub.3")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/19 08:38
-	244	(nitridization nitride nitriding nitridizing) near4 (ald atomic adj layer adj deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 07:41
-	18	(nitridization nitride nitriding nitridizing) near6 (ald atomic adj layer adj deposition) near6 (ammonia "NH.sub.3")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:01
-	1	(nitridization nitride nitriding nitridizing) near6 (ald atomic adj layer adj deposition) and ("without" near3 (ammonia "NH.sub.3"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:02
-	179	(nitridization nitride nitriding nitridizing) and silicon adj nitride and ("without" near3 (ammonia "NH.sub.3"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:03
-	96	(nitridization nitride nitriding nitridizing) and silicon adj nitride and (spacer barrier) and ("without" near3 (ammonia "NH.sub.3"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:03
-	4	(nitridization nitride nitriding nitridizing) and silicon adj nitride and (spacer barrier) and ("without" near3 (ammonia "NH.sub.3")) and (ald atomic adj layer adj deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:05
-	4	(nitridization nitride nitriding nitridizing) and ("Si.sub.3 N.sub.4" silicon adj nitride) and (spacer barrier) and ("without" near3 (ammonia "NH.sub.3")) and (ald atomic adj layer adj deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:06
-	4	(nitridization nitride nitriding nitridizing) and ("Si.sub.3N.sub.4" silicon adj nitride) and (spacer barrier) and ("without" near3 (ammonia "NH.sub.3")) and (ald atomic adj layer adj deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:06
-	4	(nitridization nitride nitriding nitridizing) and ("Si.sub.3"$1"N.sub.4" silicon adj nitride) and (spacer barrier) and ("without" near3 (ammonia "NH.sub.3")) and (ald atomic adj layer adj deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:06
-	4	("Si.sub.3"$1"N.sub.4" silicon adj nitride) and (spacer barrier) and ("without" near3 (ammonia "NH.sub.3")) and (ald atomic adj layer adj deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:06
-	5	("Si.sub.3"$1"N.sub.4" silicon adj nitride) and ("without" near3 (ammonia "NH.sub.3")) and (ald atomic adj layer adj deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:07
-	171	(ald atomic adj layer adj deposition).ti,ab,clm. and silicon adj nitride.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:08

-	2	(ald atomic adj layer adj deposition).ti,ab,clm. and silicon adj nitride.ti,ab,clm. and ("without" near4 (ammonia "NH.sub.3"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:10
-	31	pdf adj solutions.as.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:10
-	0	pdf adj solutions.as. and nitride.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:21
-	2691	((257/288) or (257/408) or (257/409) or (257/410) or (257/411)).CCLS.	USPAT; US-PGPUB	2004/10/19 08:37
-	3	(((257/288) or (257/408) or (257/409) or (257/410) or (257/411)).CCLS.) and "without" near3 (ammonia "NH.sub.3")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/19 08:38
-	1	(((257/288) or (257/408) or (257/409) or (257/410) or (257/411)).CCLS.) and "without" near3 (ammonia "NH.sub.3") and (lightly adj doped adj drain lightly-doped adj drain ldd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:26
-	5	(((257/288) or (257/408) or (257/409) or (257/410) or (257/411)).CCLS.) and (ald atomic adj layer adj deposition) and (ldd lightly adj doped adj drain) and (silicon adj nitride "Si.sub.3"$1"N.sub.4" SiN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:36
-	0	(((257/288) or (257/408) or (257/409) or (257/410) or (257/411)).CCLS.) and (nitride near4 ("without" near4 (ammonia "NH.sub.3"))) and (ldd lightly adj doped adj drain) and (silicon adj nitride "Si.sub.3"$1"N.sub.4" SiN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:37
-	1	(((257/288) or (257/408) or (257/409) or (257/410) or (257/411)).CCLS.) and ("without" near4 (ammonia "NH.sub.3")) and (ldd lightly adj doped adj drain) and (silicon adj nitride "Si.sub.3"$1"N.sub.4" SiN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:42
-	0	(((257/288) or (257/408) or (257/409) or (257/410) or (257/411)).CCLS.) and ("without" near4 (ammonia "NH.sub.3")) and (ldd lightly adj doped adj drain) and (silicon adj nitride "Si.sub.3"$1"N.sub.4" SiN) and spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:49
-	0	(NO-nitridi?ation "N.sub.2"$1O-nitridi?ation) and silicon adj nitride and (roxnox ono oxide-nitride-oxide "oxide/nitride/oxide") and (lightly adj doped adj drain ldd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:52
-	0	(NO-nitridi?ation "N.sub.2"$1O-nitridi?ation) and silicon adj nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:52
-	4	((NO "N.sub.2"$1O) near3 nitridi?ation) and silicon adj nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 16:00
-	0	(atomic adj layer adj deposition ald pecvd plasma adj enhanced adj chemical adj vapo$r adj deposition) near5 "N.sub.2" near5 ("SiCl.sub.4" "SiF.sub.4") and (ono roxnox oxide-nitride-oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 16:03

-	12	(atomic adj layer adj deposition ald pecvd plasma adj enhanced adj chemical adj vapo$r adj deposition) near5 "N.sub.2" near5 ("SiCl.sub.4" "SiF.sub.4")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 16:08
-	282	method near6 ono.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 16:09
-	0	method near6 ono.clm. and silicon adj nitride and (nitridization nitridisation) near4 (ald atomic adj layer adj deposition pecvd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 16:10
-	207	method near6 ono.clm. and silicon adj nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 16:10
-	22	method near6 ono.clm. and silicon adj nitride and (lightly adj doped adj drain ldd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 16:13
-	1	method near6 ono.clm. and silicon adj nitride and ("SiF.sub.4" "SiCl.sub.4") and (lightly adj doped adj drain ldd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 16:21
-	13	penetration near4 nitrogen and (ono roxnox oxide-nitride-oxide) and silicon adj nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 16:52
-	1	N-containing adj gas and silicon adj nitride and spacer and (ldd lightly adj doped adj drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 16:56
-	1	N-containing adj gas and silicon adj nitride and spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 16:56
-	8	N-containing adj gas and silicon adj nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 16:57
-	311	method near3 (ono oxide-nitride-oxide roxnox)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 16:58
-	137	method near3 (ono oxide-nitride-oxide roxnox).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 17:18
-	85	(oxide-nitride-oxide ono roxnox) and (ldd lightly adj doped adj drain) and spacer and etch adj stop	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 17:27
-	8	etch adj stop adj layer near3 silicon adj nitride and silicon adj nitride near4 barrier and (ldd lightly adj doped adj drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 17:56

-		112	(ldd lightly adj doped adj drain).ti,ab,clm. and silicon adj nitride and ono and 438/$9.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 18:00
-		0	(ldd lightly adj doped adj drain).ti,ab,clm. and silicon adj nitride and ono and 438/$9.ccls. and (ald atomic adj layer adj deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 18:01
-		17	(ldd lightly adj doped adj drain).ti,ab,clm. and silicon adj nitride and ono and 438/$9.ccls. and (ald atomic adj layer adj deposition pecvd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 18:01
-		17	(ldd lightly adj doped adj drain).ti,ab,clm. and silicon adj nitride and ono and 438/$9.ccls. and (ald atomic adj layer adj deposition pecvd plasma adj enhanced adj chamical adj vapor adj deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 18:02
-		1	double near4 silicon adj nitride and (ono roxnox oxide-nitride-oxide) and spacer and (ldd lightly adj doped adj drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 07:46
-		4	double near4 silicon adj nitride and (ono roxnox oxide-nitride-oxide) and spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 07:47
-		84	method near4 silicon adj nitride near4 spacer and (ldd lightly adj doped adj drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 07:51
-		3	method near4 silicon adj nitride near4 spacer and (ldd lightly adj doped adj drain) and (ald atomic adj layer adj deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 08:25
-		3	(method near4 silicon adj nitride near4 spacer and (ldd lightly adj doped adj drain) and (ald atomic adj layer adj deposition)) and (nitride adj oxide NO "N.sub.20")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 08:28
-		0	(method near4 silicon adj nitride near4 spacer and (ldd lightly adj doped adj drain) and (ald atomic adj layer adj deposition)) and (nitride adj oxide "N.sub.20")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 08:29
-		0	(method near4 nitridization and (ldd lightly adj doped adj drain) and (ald atomic adj layer adj deposition)) and (nitride adj oxide "N.sub.20")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 08:29
-		0	(method near4 nitridization) and (ldd lightly adj doped adj drain) and (ald atomic adj layer adj deposition) and (nitride adj oxide "N.sub.20")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 08:30
-		0	(method near4 nitridization) and (ald atomic adj layer adj deposition) and (nitride adj oxide "N.sub.20")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 08:30
-		0	(method near4 nitridization) near6 (nitride adj oxide "N.sub.20")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 08:30

–	0	method near4 nitridization and ("no" adj2 ammonia)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 08:31
–	47	method near4 nitridization	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 08:31
–	14	(method near4 nitridization).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 08:31
–	3	((method near4 nitridization).ti,ab,clm.) not (ammonia "NH.sub.3")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 08:32
–	3	((method near4 nitridization).ti,ab,clm.) not (ammonia "NH.sub.3") and method near4 nitridization	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 08:36
–	16	(US-6756634-$ or US-6436848-$ or US-5674788-$ or US-6690046-$ or US-6744098-$ or US-6649543-$ or US-6323519-$ or US-6653184-$ or US-6682979-$ or US-6686298-$ or US-5734185-$).did. or (US-20040146644-$ or US-20040137742-$ or US-20030143792-$ or US-20020137296-$ or US-20040042307-$).did.	USPAT; US-PGPUB	2004/10/18 09:17
–	0	((US-6756634-$ or US-6436848-$ or US-5674788-$ or US-6690046-$ or US-6744098-$ or US-6649543-$ or US-6323519-$ or US-6653184-$ or US-6682979-$ or US-6686298-$ or US-5734185-$).did. or (US-20040146644-$ or US-20040137742-$ or US-20030143792-$ or US-20020137296-$ or US-20040042307-$).did.) and fu.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 09:36
–	27	ldd and spacer and silicon adj nitride and ono and ild	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 10:16
–	28	ild near4 protect$3 and gate and silicon adj nitride and spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 10:16
–	2	("20020146879").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 15:19